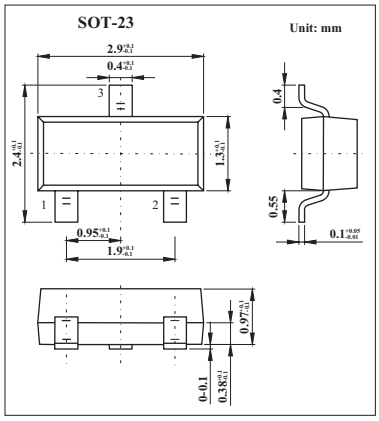
Silicon Switching Diode

BAR74



Features

- For high-speed switching applications

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Reverse voltage	V_R	50	V
Peak reverse volatge	V_{RM}	50	V
Forward current	I_F	250	mA
Surege forward current, T = 1 μ s	I_{FS}	4.5	A
Total power dissipation, Ts = 54 ℃	P_{tot}	370	mW
Junction temperature	T_j	150	℃
Storage temperature range	T_{stg}	-65 to +150	℃
Junction ambient (Note 1)	$R_{th\ JA}$	⩽ 330	K/W
Junction soldering point	$R_{th\ JS}$	⩽ 260	K/W

Note

1. Package mounted on epoxy pcb 40 mm × 40 mm × 1.5 mm/6 cm^2 Cu.

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Breakdown voltage	V_R	I_R =100 μ A	50			V
Forward voltage	V_F	I_F = 100 mA			1	V
Reverse current	I_R	V_R = 50 V			0.1	μ A
		V_R = 50 V,Ta = 150 ℃			100	
Diode capacitance	C_D	V_R = 0 V,f = 1 MHz			2	pF
Reverse recovery time	t_{rr}	I_F = I_R = 10 mA,R_L = 100 Ω ,measured at I_R = 1 mA			4	ns

Marking

Marking	JBs